



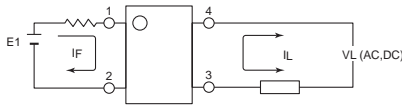
Parameter	Symbol	Rating	Units
Load Voltage	$V_L$	60	V
Load Current	$I_L$	1.1	A
On-Resistance	$R_{on}$	0.27	$\Omega$
I/O Breakdown Voltage	$V_{io}$	5000	Vrms



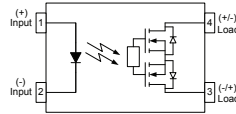
SMD-4



DIP-4



AC/DC



1. LED Anode
2. LED Cathode
- 3.4. Drain(MOS FET)

### APSEMI PhotoRelays

APSEMI Photorelays are the most reliable, technically advanced logic-to-power interface devices. Their basic function is to take a low current signal from a microprocessor to control the switching of both AC and DC loads, while providing an isolation barrier between logic and power. While this function is common to all relays, Photorelays provide distinct advantages over their mechanical counterparts including:

- Long life (No limit on mechanical and electrical lifetime)
- Bounce-free switching
- Higher speed and high frequency switching
- Higher sensitivity (less power consumption)
- Immunity to EMI or RFI
- No have voltaic arc, bounce, and noise
- More resistant to vibration and impact
- AC or DC load switching
- Small package size

### Function

APSEMI PhotoRelays operate by taking a low level input current (<5mA) that energizes an input Infrared LED, which is optically-coupled to a Photo-diode array chip. This IC in turn generates a photo voltage that powers two MOSFETs typically connected in a source-to-source configuration, allowing for both AC and DC output loads. Photorelay basically move photons to accomplish their switching function, they incur no mechanical wear and tear, providing consistent reliable switching.

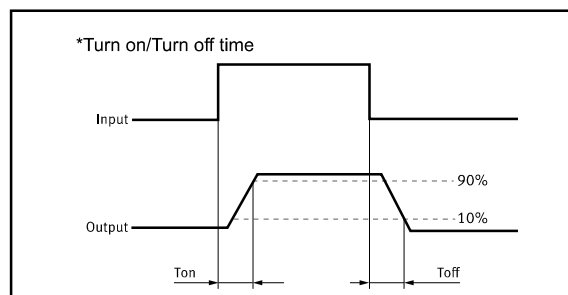
### Applications

These advantages make APSEMI Photorelays the ideal choice for:

- Telecom/Datacom switching
- Multiplexers
- Meter reading systems
- Data acquisition
- Medical equipment
- Battery monitoring
- I/O Sub-Systems
- Robotics
- Aerospace
- Home/Safety security systems
- Process Control
- Energy Management
- Reed Relay EMR Replacement
- Programmable Controllers

### TPYES

Category	Output Rating		Package	Part No.	Packing Quantity
	Load Voltage	Load Current			
AC/DC	60V	1.1A	DIP-4	APY211G1E	50pcs /tube
			SMD-4	APY211G1EH	1000pcs /reel



**Absolute Maximum Ratings** (Ta = 25°C)

Item		Symbol	Value	Units	Note
Input	Continuous LED Current	$I_F$	50	mA	
	Peak LED Current	$I_{FP}$	1000	mA	f=100Hz, duty=1%
	LED Reverse Voltage	$V_R$	5	V	
	Input Power Dissipation	$P_{In}$	75	mW	
Output	Load Voltage	$V_L$	60	V(AC peak or DC)	
	Load Current	$I_L$	1.1	A	
	Peak Load Current	$I_{Peak}$	3.0	A	100ms(1 pulse)
	Output Power Dissipation	$P_{out}$	380	mW	
Total Power Dissipation		$P_T$	450	mW	
I/O Breakdown Voltage		$V_{I/O}$	5000	Vrms	RH=60%, 1min
Operating Temperature		$T_{opr}$	-40 to 85	°C	
Storage Temperature		$T_{sig}$	-40 to 100	°C	
Pin Soldering Temperature		$T_{sol}$	260	°C	10 sec max.

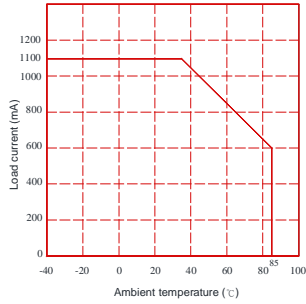
**Electrical Characteristics** (Ta = 25°C)

Item		Symbol	MIN.	TYP.	MAX.	Units	Conditions
Input	LED Forward Voltage	$V_F$		1.2	1.4	V	$I_F=10mA$
	Operation LED Current	$I_{Fon}$		0.5	5.0	mA	
	Recovery LED Current	$I_{Foff}$		0.35	0.5	mA	
	Recovery LED Voltage	$V_{Foff}$	0.7			V	
Output	On-Resistance	$R_{on}$		0.27	0.7	$\Omega$	$I_F=5mA, I_L=100mA,$ Time to flow is within 1 sec.
	Off-State Leakage Current	$I_{Leak}$			1	$\mu A$	$V_L=Rating$
	Output Capacitance	$C_{out}$		115		pF	$V_L=0, f=1MHz$
Transmis sion	Turn-On Time	$T_{on}$		1.5	5	ms	$I_F=5mA, I_L=100mA,$
	Turn-Off Time	$T_{off}$		0.05	2	ms	
Coupled	I/O Isolation Resistance	$R_{I/O}$	$10^{10}$			$\Omega$	DC500V
	I/O Capacitance	$C_{I/O}$		0.8	1.5	pF	f=1MHz

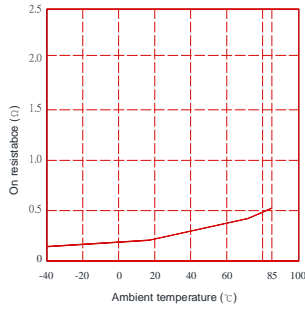


## Engineering Data

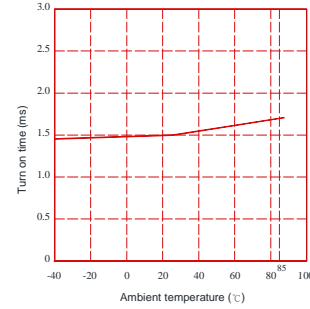
Load current Vs. Ambient temperature



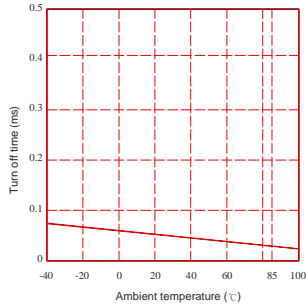
On resistance Vs. Ambient temperature



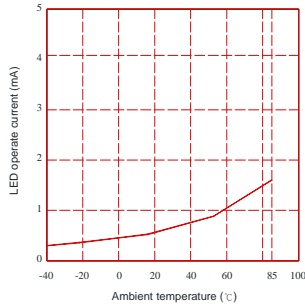
Turn on time Vs. Ambient temperature



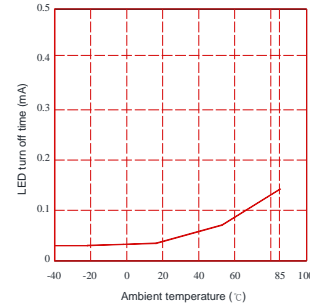
Turn off time Vs. Ambient temperature



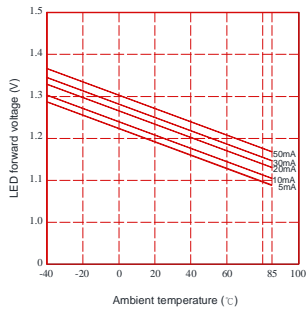
LED operate current Vs. Ambient temperature



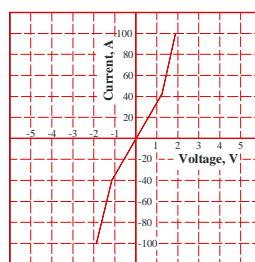
LED turn off time Vs. Ambient temperature



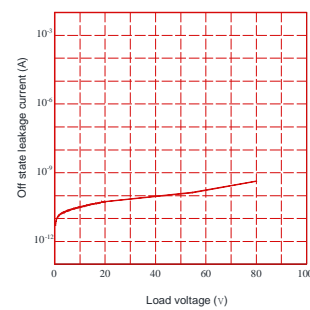
LED forward voltage Vs. Ambient temperature



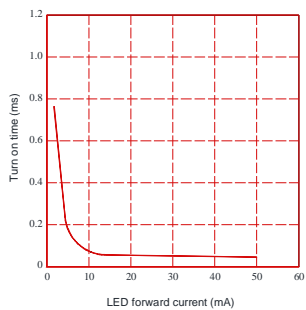
Voltage Vs. current characteristics of output at MOS portion



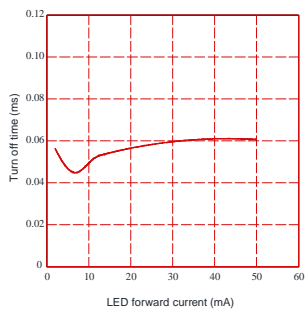
Off state leakage current Vs. Load voltage characteristics



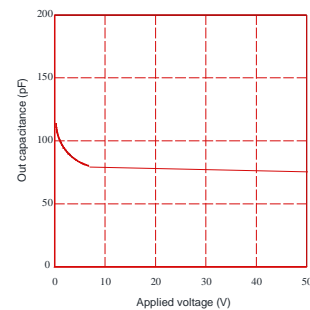
LED forward current Vs. turn on time characteristics



LED forward current Vs. turn off time characteristics



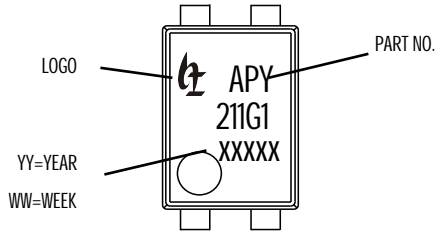
Applied voltage Vs. output capacitance characteristics



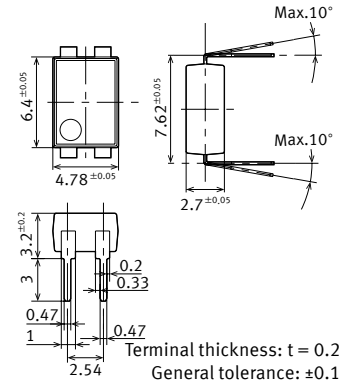


### Dimensions and DIP-4 Package Unit: mm

#### Marking



#### Surface mount terminal type

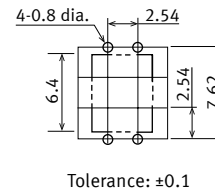


#### Lable



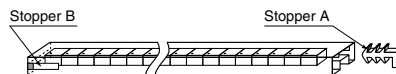
#### PC board pattern

(BOTTOM VIEW)



### DIP Type dimensions Unit: mm inch Tolerance: +0.2 +.007

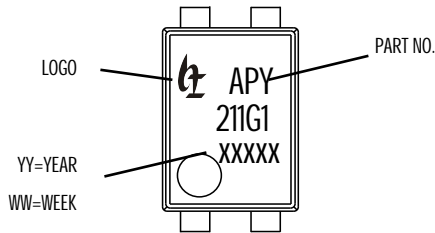
Devices are packaged in a tube so that pin No. 1 is on the stopper B side. Observe correct orientation when mounting them on PC boards.



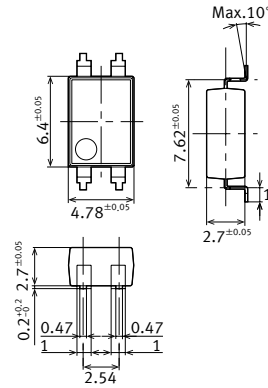


### Dimensions and SMD-4 Package Unit: mm

#### Marking

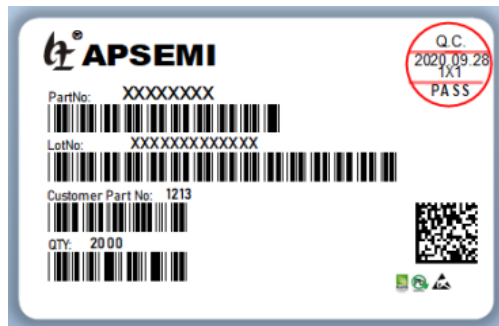


#### Surface mount terminal type

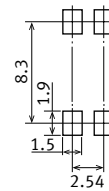


Terminal thickness: t = 0.2  
General tolerance: ±0.1

#### Lable

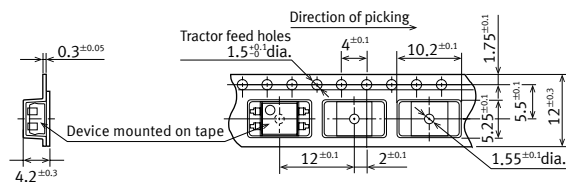
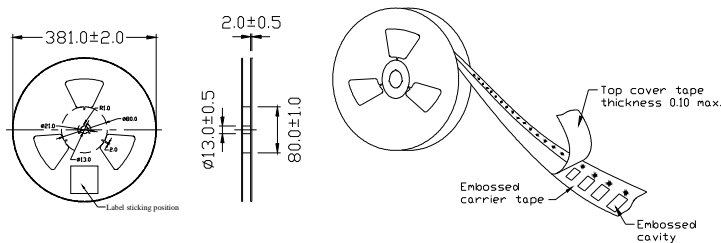


#### Recommended mounting pad (TOP VIEW)



Tolerance: ±0.1

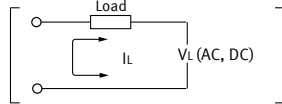
### Tape dimensions ( tape reel )





## Using Methods

Examples of resistance value to control LED forward current ( $I_F=5\text{mA}$ )



E1	R1 (Approx)
3.3V	300 $\Omega$
5.0V	600 $\Omega$
12V	1.9K $\Omega$
24V	4.1K $\Omega$

LED forward current must be more than 5mA , at  $I(\text{MIN})$  ,and less than 30mA , at  $I(\text{MAX})$ .



## Recommended Operating Conditions

Please obey the following conditions to ensure proper device operation and resetting. Input LED current (Recommended value):

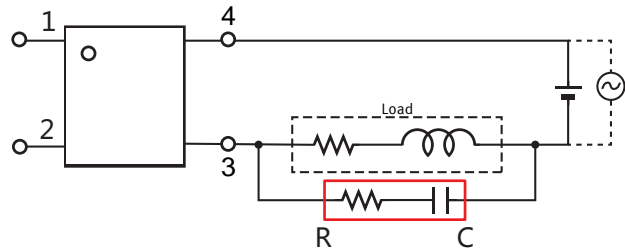
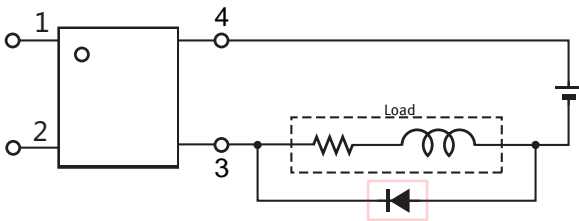
Characteristic	Symbol	Min	Typ.	Max	Unit
Forward current	$I_F$	5.0	7.0	30	mA

## Protection Circuit

Output spike voltages:if an inductive load generates spike voltages which exceed heabsolute maximum rating, the spike voltage shall be limited.

Clamp diode is connected in parallel with the load.  
Absorb capacity with external diode.

CR Snubber is connected in parallel with the load.  
Absorb capacity with buffer capacity.



When adding diodes, buffer circuits (C-R), and other protections, they need to be installed near the MOS RELAY to be effective. Adding protection elements may result in a slow reset time, so adjust them according to the actual situation before use.

Note: When developing designs using this product, perform the expected performance of the equipment under the operating conditions recommended by the guidelines in this document. Continuous use under heavy loads (including, but not limited to, the application of high temperatures/current/voltage and significant changes in temperature, etc.) may result in deterioration of the reliability of this product.



## Recommended Soldering Conditions

### (a) Infrared reflow soldering :

- Peak reflow soldering : 260°C or below (package surface temperature)
- Time of peak reflow temperature : 10 sec
- Time of temperature higher than 230°C : 30-60 sec
- Time to preheat temperature from 180~190°C : 60-120 sec
- Time(s) of reflow : Two
- Flux : Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

### Recommended Temperature Profile of Infrared Reflow



### (b) Wave soldering :

- Temperature : 260°C or below (molten solder temperature)
- Time : 10 seconds or less
- Preheating conditions : 120°C or below (package surface temperature)
- Time(s) of reflow : One
- Flux : Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

### (c) Cautions :

- Fluxes : Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.
- Avoid shorting between portion of frame and leads.



## RESTRICTIONS ON PRODUCT USE

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